

Long-range ordering and local structural disordering of BiAgSe₂ and BiAgSeTe thermoelectric

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Table.S1 Crystallographic information of BiAgSe₂, BiAgTe₂, Bi₂Se₃

BiAgSe₂-α-phase	<i>Pm</i> $\bar{3}$ 1, SG. No.164, a=b=4.18 Å, c= 19.67Å $\alpha=\beta=90^\circ$, $\gamma=120^\circ$				
	x	y	z	Occupation	Wyckoff site
Ag	0	0	0	1	1a
Bi	0	0	0.5	1	1b
Ag	0.333333	0.666667	0.672	1	2d
Bi	0.333333	0.666667	0.163	1	2d
Se	0	0	0.253	1	2c
Se	0.333333	0.666667	0.926	1	2d
Se	0.333333	0.666667	0.406	1	2d
BiAgSe₂-β-phase	<i>R</i> $\bar{3}$ <i>m</i> , SG No.166, a=b= 4.201Å, c=18.865 Å $\alpha=\beta=90^\circ$, $\gamma=120^\circ$				
	x	y	z	Occupation	Wyckoff site
Ag	0	0	0	1	3a
Bi	0	0	0.5	1	3b
Se	0	0	0.254	1	6c
BiAgSe₂-γ-phase	<i>Fm</i> $\bar{3}$ <i>m</i> , SG No.225, a=b= 5.832Å $\alpha=\beta=90^\circ$, $\gamma=120^\circ$				
	x	y	z	Occupation	Wyckoff site
Ag	0	0	0	0.5	4a
Se	0.5	0.5	0.5	1	4b
Bi	0	0	0	0.5	4a
BiAgTe₂	<i>R</i> $\bar{3}$ <i>m</i> , SG No.166, a=b= 4.453Å, c=20.954 Å $\alpha=\beta=90^\circ$, $\gamma=120^\circ$				
	x	y	z	Occupation	Wyckoff site
Ag	0	0	0	1	3a
Bi	0	0	0.5	1	3b
Te	0	0	0.744	1	6c

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Bi₂Se₃		<i>R</i> $\bar{3}$ <i>m</i> , SG No.166, a=b= 4.191Å, c=29.929Å			
		$\alpha=\beta=90^\circ, \gamma=120^\circ$			
	x	y	z	Occupation	Wyckoff site
Bi	0	0	0.398	1	6c
Se	0	0	0.216	1	6c
Se	0	0	0	1	3a

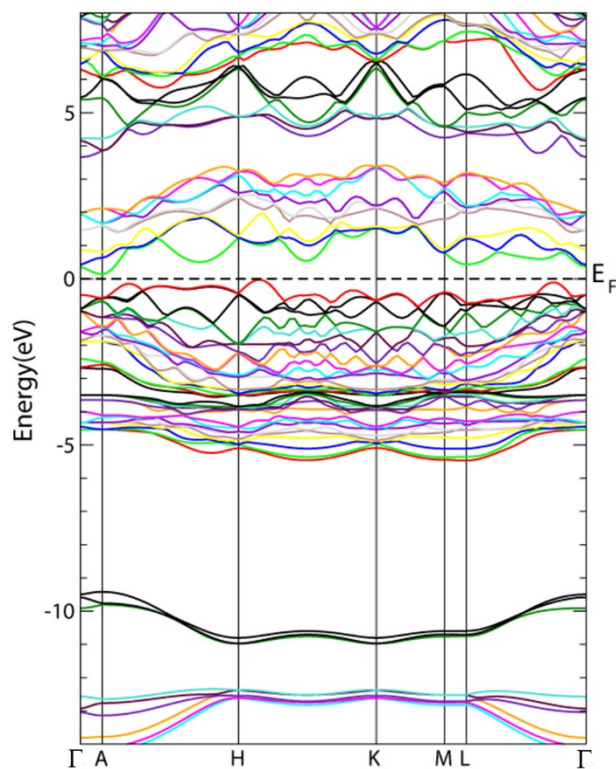


Figure.S1 Electronic band structure of α -BiAgSe₂

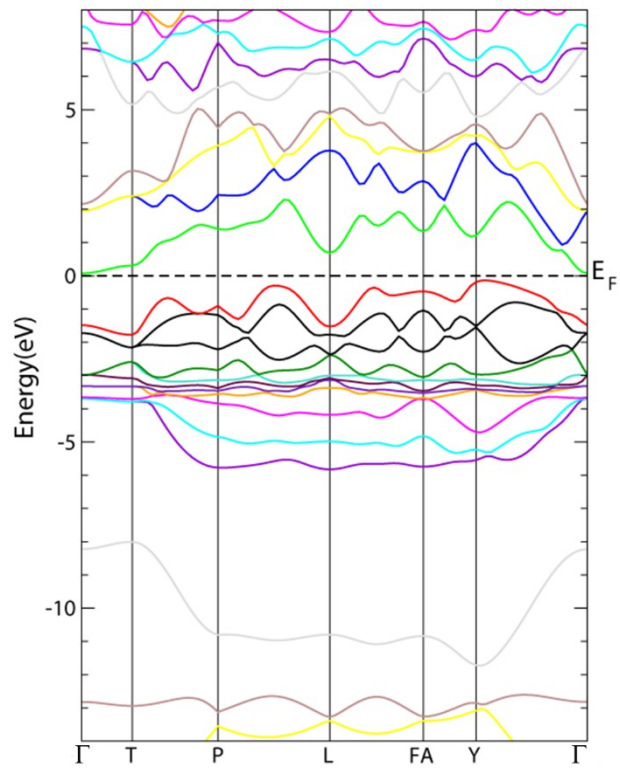


Figure.S2 Electronic band structure of β -BiAgSe₂

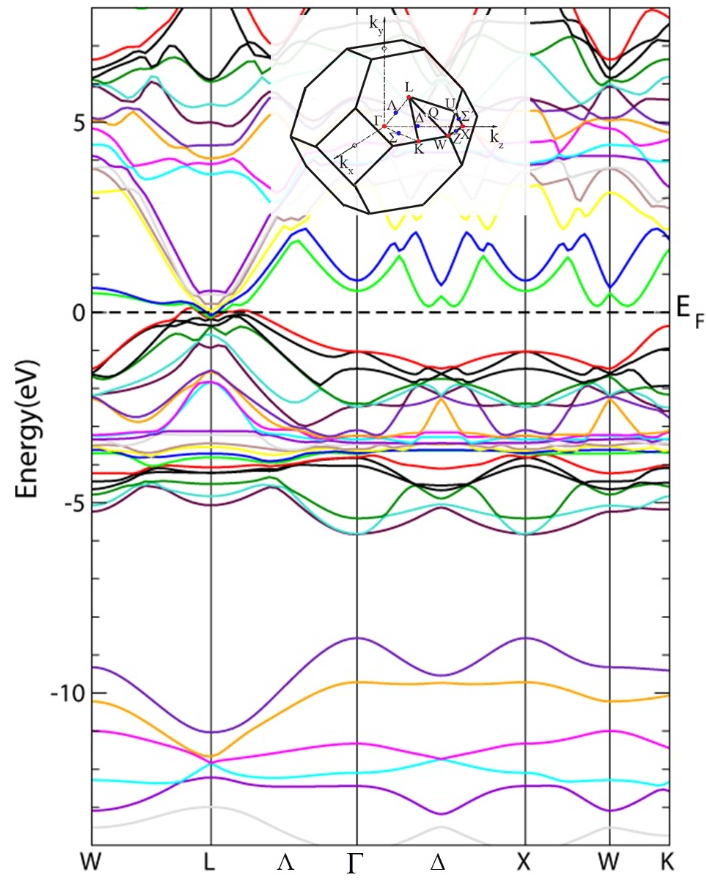


Fig.S3 Electronic Band structure of cubic BiAgSeTe; the inset figure shows the first Brillouin zone (BZ) of BiAgSeTe with high-symmetry points (red points) for calculations.

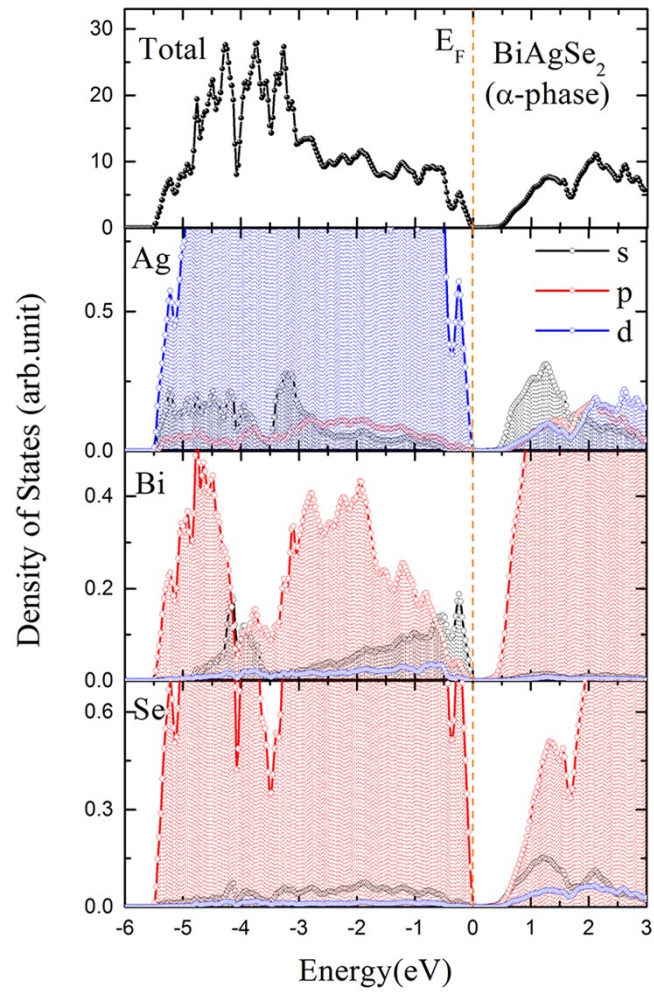


Figure.S4 Projected partial density of electronic states for α -phase BiAgSe_2

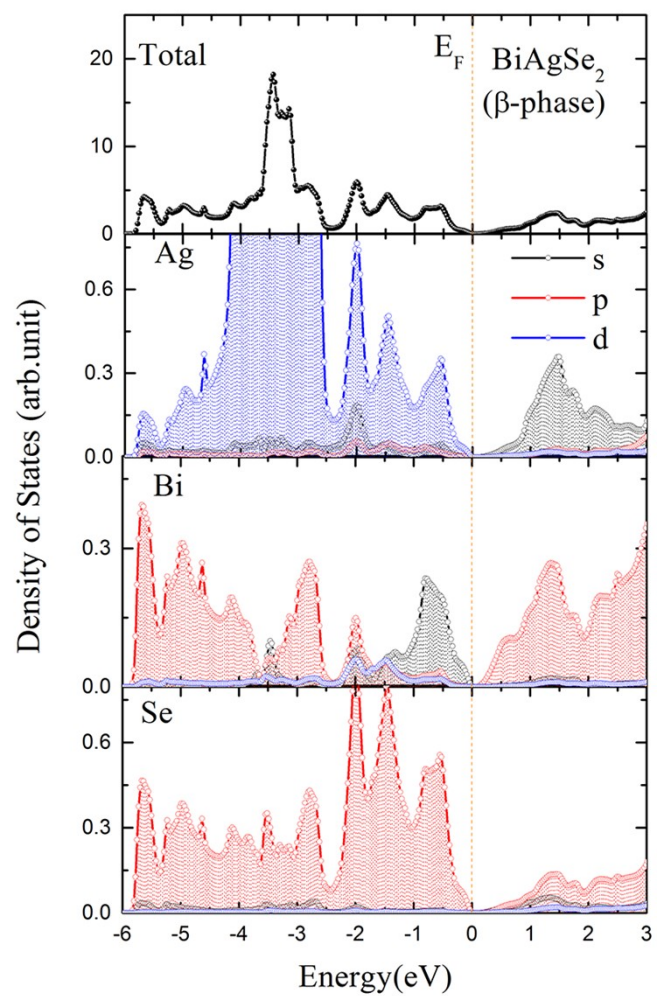


Figure.S5 Projected partial density of electronic states for β -phase BiAgSe_2

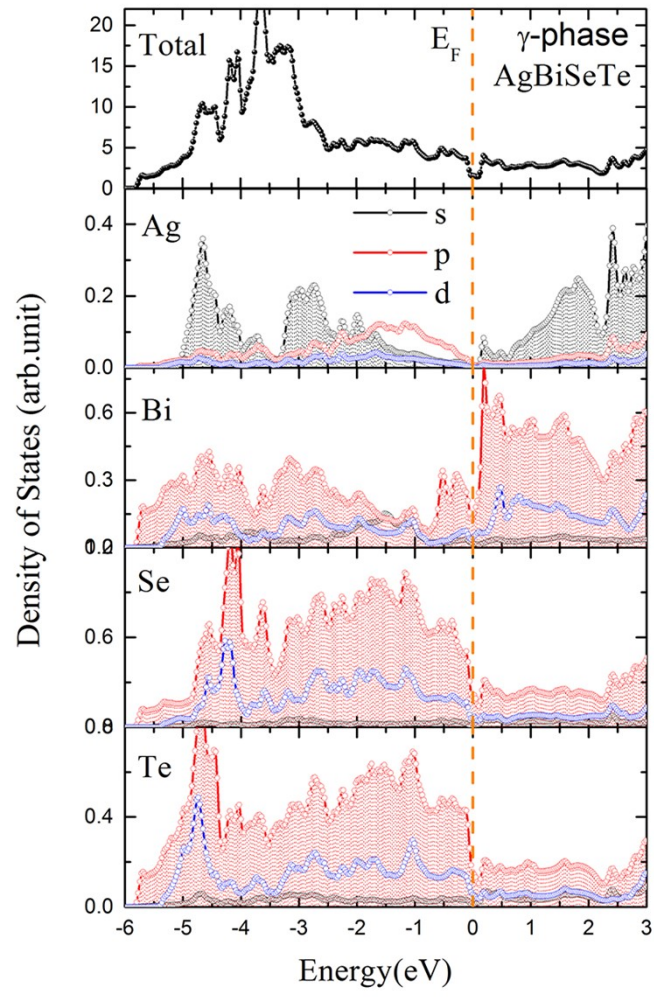


Figure.S6 Projected partial density of electronic states for γ -phase BiAgSeTe

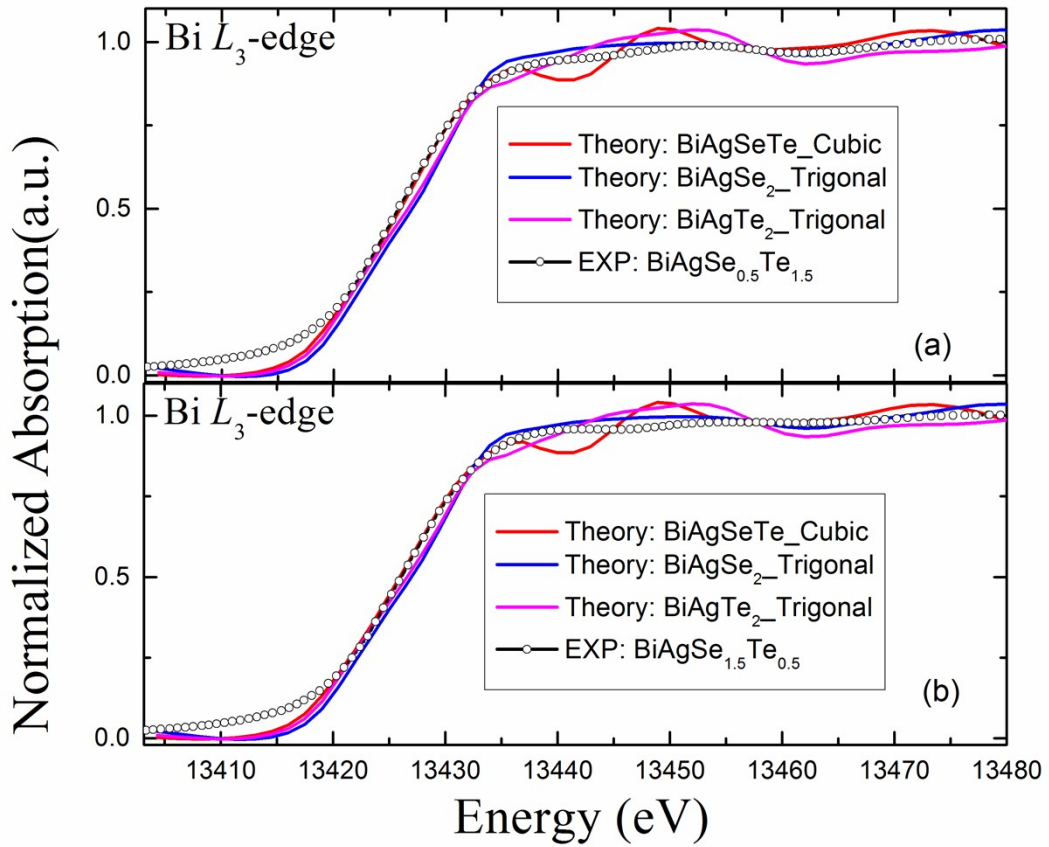


Figure.S7 Comparison of experimental and theoretical XANES spectra at Bi L_3 -edge for (a) $\text{BiAgSe}_{0.5}\text{Te}_{1.5}$, (b) $\text{BiAgSe}_{1.5}\text{Te}_{0.5}$. Note that hexagonal structures were used BiAgSe_2 and BiAgTe_2 models while cubic structure was used for BiAgSeTe .

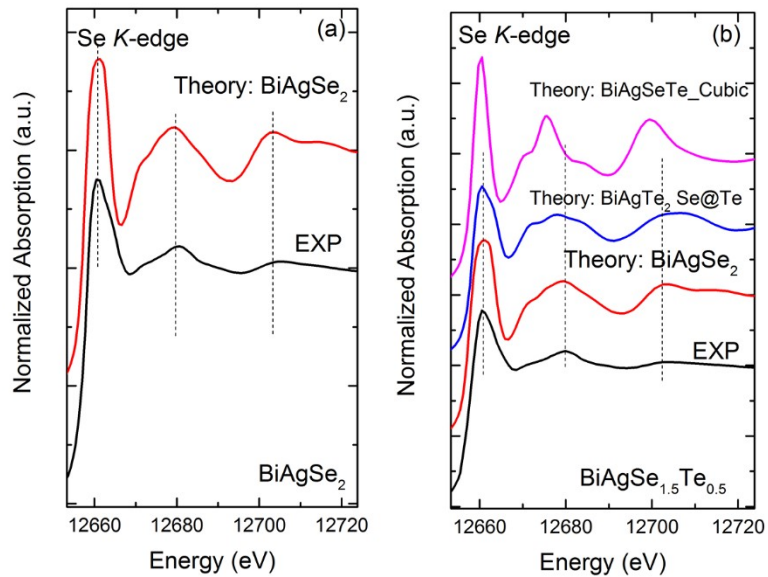


Figure.S8 Comparison of experimental and theoretical XANES spectra at Se K -edge for (a) BiAgSe_2 (b) $\text{BiAgSe}_{1.5}\text{Te}_{0.5}$. Note that hexagonal structures were used BiAgSe_2 and BiAgTe_2 models while cubic structure was used for BiAgSeTe .

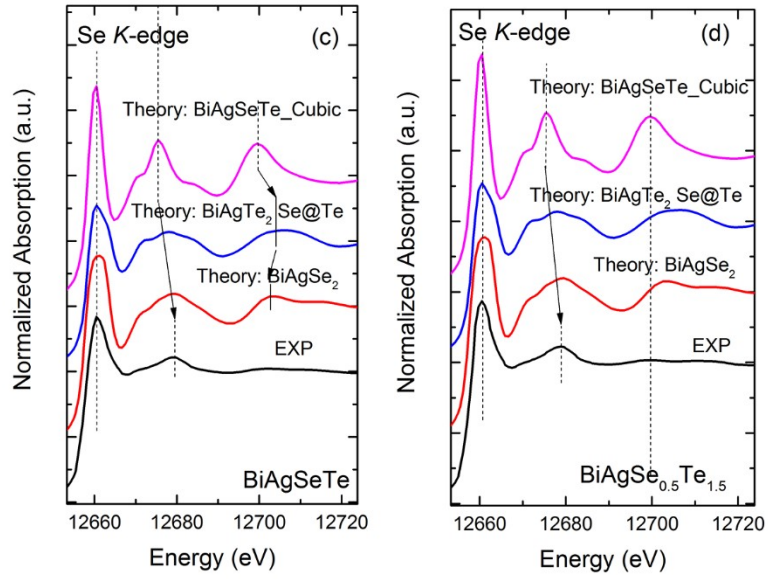


Figure.S9 Comparison of experimental and theoretical XANES spectra at Se *K*-edge for (a) BiAgSeTe (b) BiAgSe_{0.5}Te_{1.5}. Note that hexagonal structures were used BiAgSe₂ and BiAgTe₂ models while cubic structure was used for BiAgSeTe.

Table.S2. The electron number counts for *s*, *p*, *d* electrons and the differentially calculated charge transfer¹ as retrieved from the full multiple scattering theory calculations using FEFF9.0 code.

BiAgSe ₂	S	P	D	CT	BiAgTe ₂	S	P	D	CT
Ag L₃					Ag L₃				
Ag	0.731	0.518	9.879	-0.128	Ag	0.812	0.555	9.859	-0.225
Bi	1.936	2.173	10.489	0.402	Bi	1.923	2.313	10.445	0.321
Se	1.977	3.868	0.293	-0.137	Te	1.952	3.684	0.412	-0.048
BiAgSe₂					BiAgTe₂				
Bi L₃	S	P	D	CT	Bi L₃	S	P	D	CT
Ag	0.725	0.519	9.879	-0.123	Ag	0.798	0.547	9.859	-0.204
Bi	1.936	2.172	10.490	0.402	Bi	1.924	2.291	10.455	0.328
Se	1.976	3.859	0.305	-0.140	Te	1.956	3.698	10.409	-0.063
BiAgSe₂					BiAgTe₂				
Se L₃	S	P	D	CT	Te L₃	S	P	D	CT
Ag	0.745	0.503	9.879	-0.128	Ag	0.823	0.539	9.860	-0.221
Bi	1.939	2.148	10.482	0.432	Bi	1.925	2.288	10.441	0.346
Se	1.977	3.885	0.291	-0.153	Te	1.951	3.704	0.407	-0.063
BiAgSeT					BiAgSeT				
e	S	P	D	CT	e	S	P	D	CT
Ag L₃					Te L₃				
Bi	1.902	2.721	10.251	0.125	Bi	1.968	2.128	10.366	0.536
Ag	0.590	0.546	9.835	0.029	Ag	0.594	0.535	9.830	0.042

Se	1.970	4.112	0.185	-0.266	Se	1.972	4.143	0.193	-0.309
Te	1.921	3.676	0.293	0.111	Te	1.929	3.778	0.298	-0.004

Table.S3 EXAFS fitting results for different structural models at the Bi L_3 -edge

CN: coordination number, R: bond distance, σ^2 : means square relative displacement, ΔE : energy shift; R-factor: fitting quality

Samples	Path	CN	R	$\sigma^2 (\times 10^3)$	ΔE	R-factor
BiAgSe ₂ -Bi ₂ Se ₃	Bi-Se1	3.0	2.8670±0.0889	11.3±11.0	5.6±4.7	0.02
	Bi-Se2	2.7	3.0748±0.1308	13.0±5.5	5.6±4.7	
BiAgSe ₂ - β -phase	Bi-Se	1.9	2.7923±0.0336	12.0±4.6	-9.9±5.2	0.06
BiAgSeTe- Bi ₂ Se ₃	Bi-Se1	0.8	2.8971±0.1890	31.3±7.2	18.6±15.1	0.31
	Bi-Se2	0.9	3.1330±0.4263	75.4±17.1	18.6±15.1	

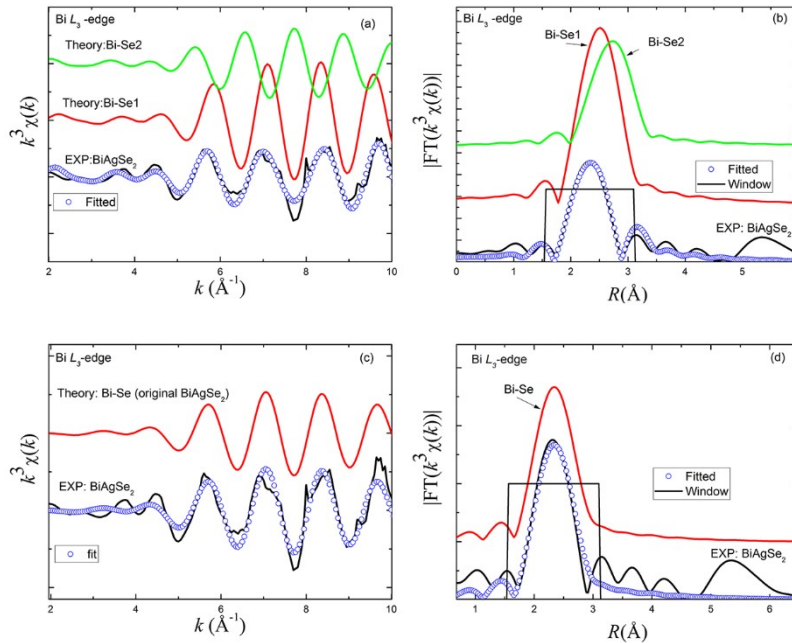


Figure.S10 Best fit of the Bi L_3 -edge EXAFS of BiAgSe₂ in k-space (left panel) and R-space (right panel) by using (a, b) distorted model structure with two Bi-Se bond lengths and (c,d) the original hexagonal with one Bi-Se bond lengths

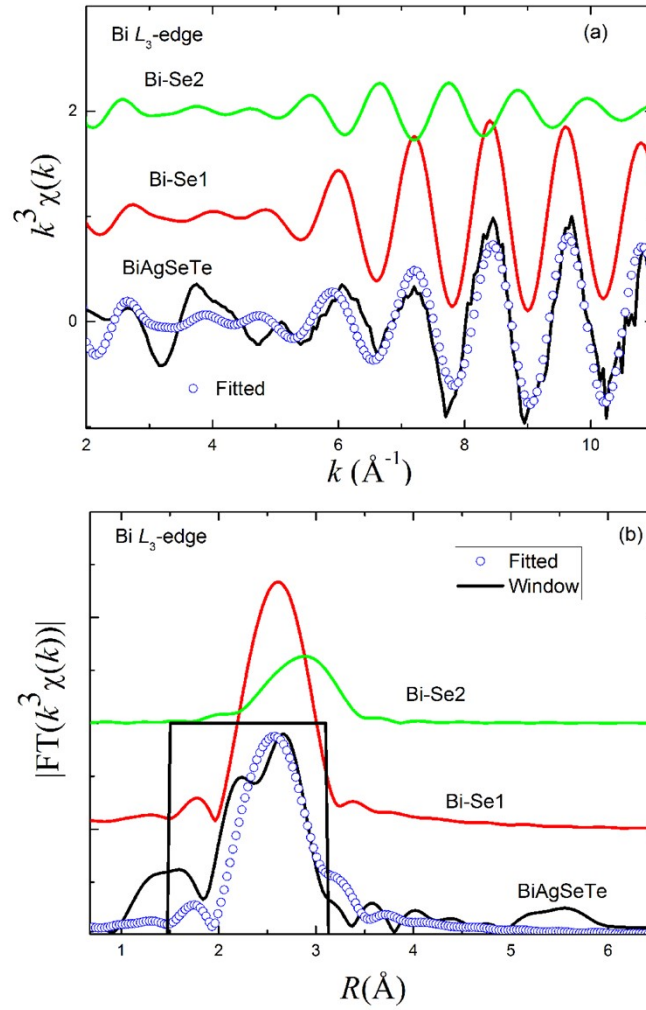


Figure.S11 Best fit of the Bi L_3 -edge EXAFS of BiAgSeTe in k-space (a) and R-space (b) by using distorted model structure with two Bi-Se bond lengths

Table.S4 EXAFS fitting results for different structural models at the Se K-edge

BiAgSe₂	Path	CN	R	$\sigma^2 (\times 10^{-3})$	ΔE	R-factor
k^3 weighted, k range $\in (2.0-9.7) \text{ \AA}^{-1}$ R range $\in (1.5-3) \text{ \AA}$						
BiAgSe₂-β-phase	Se-Ag	2.7	2.7407 \pm 0.0889	26.59 \pm 11.0	1.3 \pm 1.1	0.04
	Se-Bi	2.3	2.8656 \pm 0.1308	17.0 \pm 5.5	1.3 \pm 1.1	
BiAgSeTe	Path	CN	R	$\sigma^2 (\times 10^{-3})$	ΔE	R-factor
k^3 weighted, k range $\in (2.0-11) \text{ \AA}^{-1}$ R range $\in (1-3) \text{ \AA}$						

BiAgSe₂-β-phase	Se-Ag	0.3	2.6471±0.0482	12.3±6.3	2.4±0.2	0.14
	Se-Bi	2.5	2.8020±0.0817	25.6±17.8	2.4±0.2	
BiAgSeTe k³ weighted, k range ∈ (2.0-11) Å⁻¹ R range ∈ (1-3) Å	Path	CN	R	σ ² (×10 ⁻³)	ΔE	R-factor
BiAgSe₂-γ-phase	Bi-Se	0.4	2.8169±0.02	5.3±1.8	4.7±2.4	0.07
	Bi-Te	1.4	2.9926±0.07	21.7±6.1		

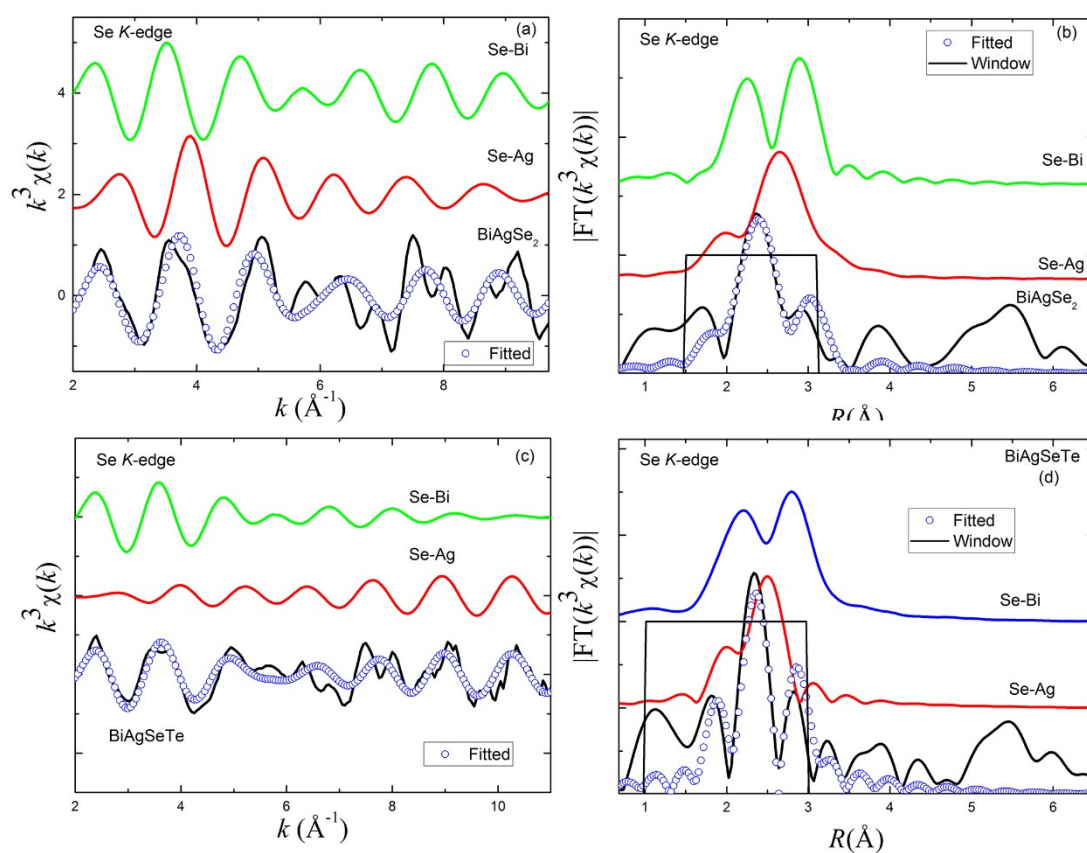


Figure.S12 Best fit of the Se K-edge EXAFS of BiAgSe₂ (a) in k-space and (b) R-space and that of BiAgSeTe (c) in k-space and (d) R-space

References

1. Ankudinov, A. L.; Ravel, B.; Rehr, J. J.; Conradson, S. D., Real-space multiple-scattering calculation and interpretation of x-ray-absorption near-edge structure. *Phys. Rev. B* **1998**, *58* (Copyright (C) 2009 The American Physical Society), 7565.